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Intensive formation of K radiative centers in silicon nitride by implantation with carbon ions

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The implantation of silicon nitride with carbon ions stimulates the formation of additional emitting centers, which are appearing growth points for silicon nanoclusters. Moreover, this method makes it possible to set the sizes of nanocrystals, change their concentration, as well as the properties of the "nanocluster - matrix" interface. All of the above makes photoluminescence controllable and increases its intensity[1,2].

Synthesis of silicon nitride thin film was carried out by PECVD method. The ratio of the reacting gases SiH4/N2 was 1/3 and 1/6 for the SiN1.1 and SiN1.5 samples, respectively. The carbon implantation fluencies were 1×10^{14} cm-2, 2×10^{15} cm-2 and 1×10^{16} cm-2 in experiment.

The spectrum of photoluminescence was detected in the minimum fluence (1×10^{14} cm-2) and subsequent annealing at 1100 °C for one-hour samples. It noted that at this annealing temperature an additional band appears with a maximum at 450 nm. This indicates that at a given annealing temperature, the presence of carbon leads to additional centers of radiative recombination. To confirm this effect, the duration of annealing at 1100 °C extended to four hours. At a given duration of annealing, a luminescence signal already appears for samples implanted with increased fluencies (2×10^{15} cm-2 and 1×10^{16} cm-2). For sample implanted fluence of 1×10^{14} cm-2 and annealed for four hours at 1100 °C, the luminescence spectrum is more intense and shifted to the short-wavelength region compare to sample with a similar annealing without pre-implantation. This confirms the participation of carbon atoms in the formation of radiative recombination centers at high annealing temperatures.

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